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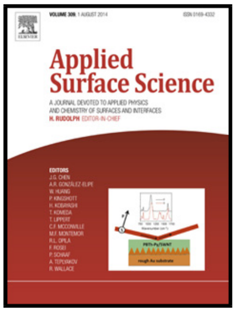

Title: The influence of deposition parameters on Ti/Pt film growth by confocal sputtering and the temperature dependent resistance behavior using SiO_x and Al_2O_3 substrates

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Highlights

- The influence of different sputtering pressure 0.5 – 8 Pa and power 100 - 500W on the microstructure as well as on crystalline and electrical properties is investigated.
- Ti/Pt films deposited on oxidized Si and on Al_2O_3 show a preferred (111) crystalline orientation, but films on Al_2O_3 have an additional polycrystalline structure
- The crystal size is influenced by annealing process.
- The highest TCR is achieved at a pressure of 1.2 Pa and a sputtering power of 100W.